

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in circuits where high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. This "series CT" triac will commute the full RMS current at the maximum rated junction temperature ( $T_j = 150\text{ °C}$ ) without the aid of a snubber where "high junction operating temperature capability" is required.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by  $dV/dt$
- High junction operating temperature capability
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

## 3. Applications

- Applications subject to high temperature
- Electronic thermostats (heating and cooling)
- Motor controls for home appliances
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

## 4. Quick reference data

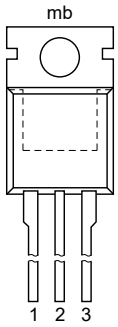
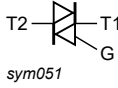
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 134\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	6	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	60	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	-	66	A
$T_j$	junction temperature		-	-	150	°C
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	4	-	35	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
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$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; Fig. 9	-	-	35	mA
$V_T$	on-state voltage	$I_T = 7\text{ A}$ ; $T_j = 25\text{ °C}$ ; Fig. 10	-	1.3	1.6	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 150\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/ $\mu\text{s}$
$di_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 150\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit	10	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 150\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit	12	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 150\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit	20	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p style="text-align: center;"><b>TO-220AB (SOT78)</b></p>	 <p style="text-align: center;"><i>sym051</i></p>
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

## 6. Ordering information

Table 3. Ordering information

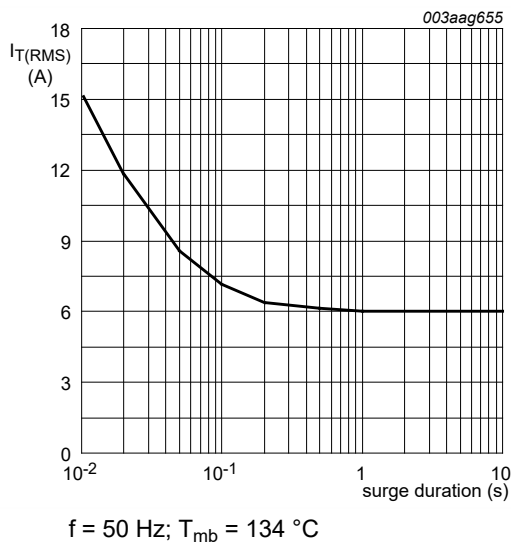
Type number	Package		
	Name	Description	Version
BTA206-800CT	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 7. Limiting values

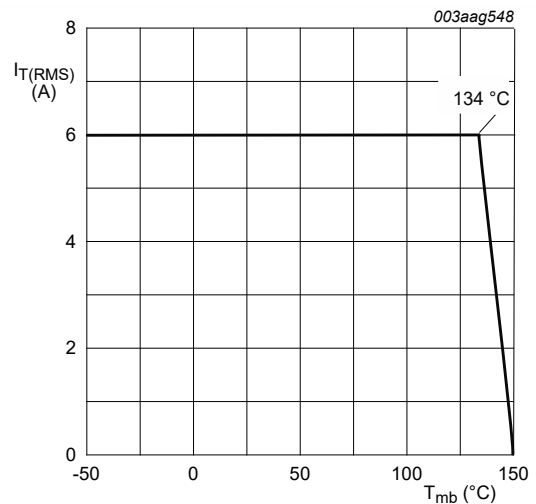
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

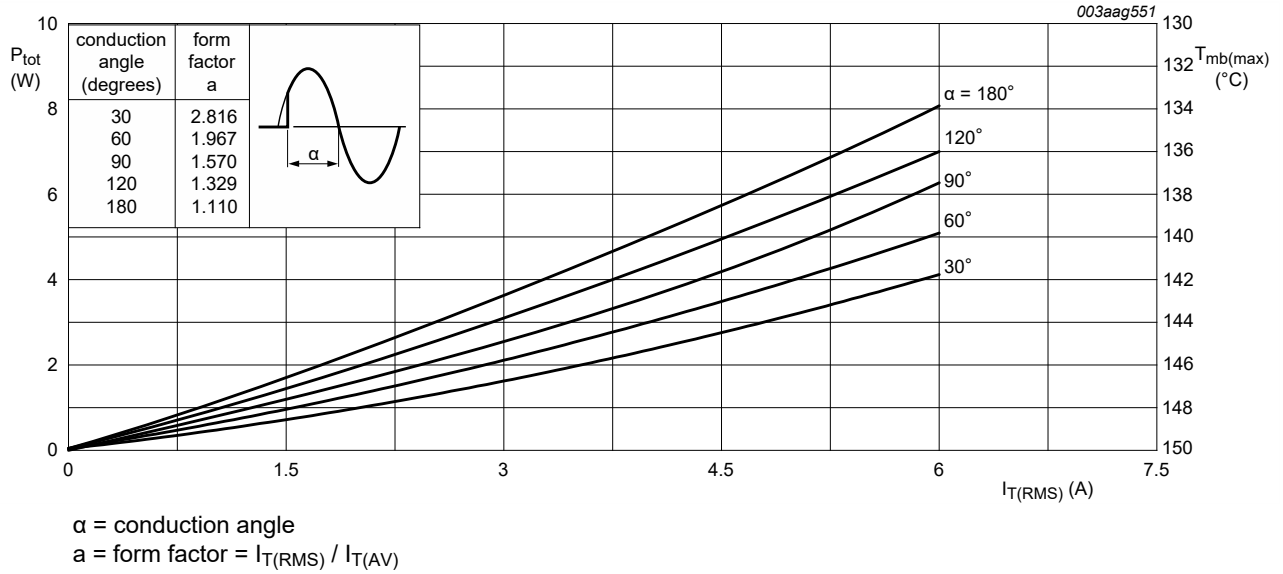
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 134\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	6	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	60	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	66	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	18	$A^2s$
$di_T/dt$	rate of rise of on-state current	$I_G = 0.2\text{ A}$	-	100	$A/\mu s$
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	$^{\circ}C$
$T_j$	junction temperature		-	150	$^{\circ}C$



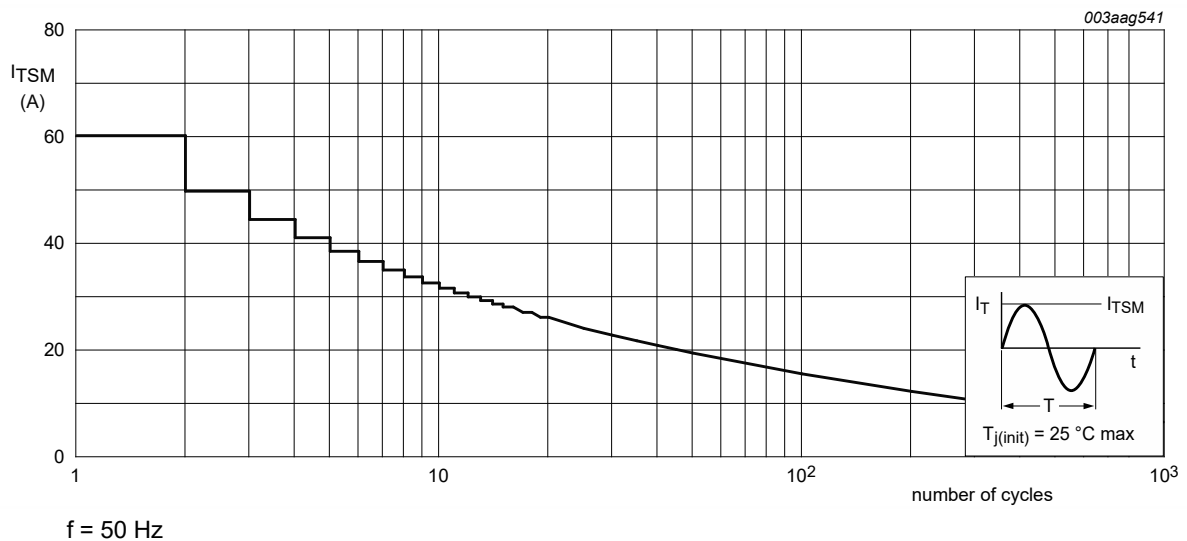
**Fig. 1. RMS on-state current as a function of surge duration; maximum values**



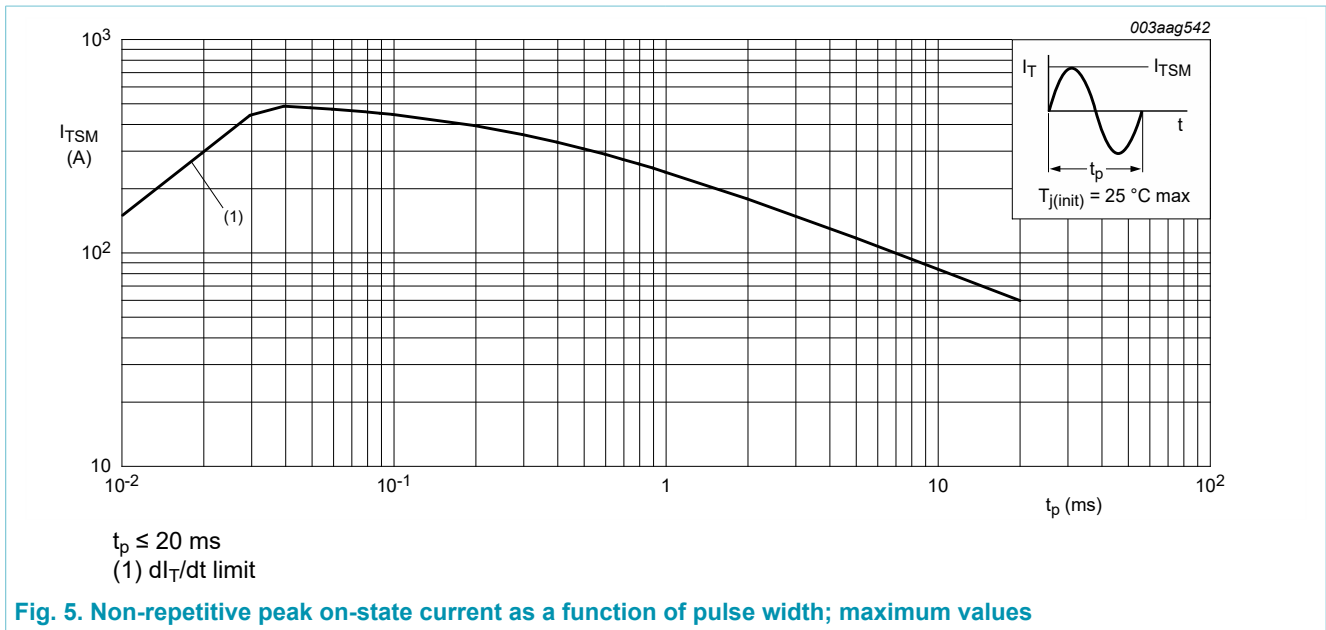
**Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values**



**Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values**



**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**



## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; <a href="#">Fig. 6</a>	-	-	2	K/W
		half cycle; <a href="#">Fig. 6</a>	-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

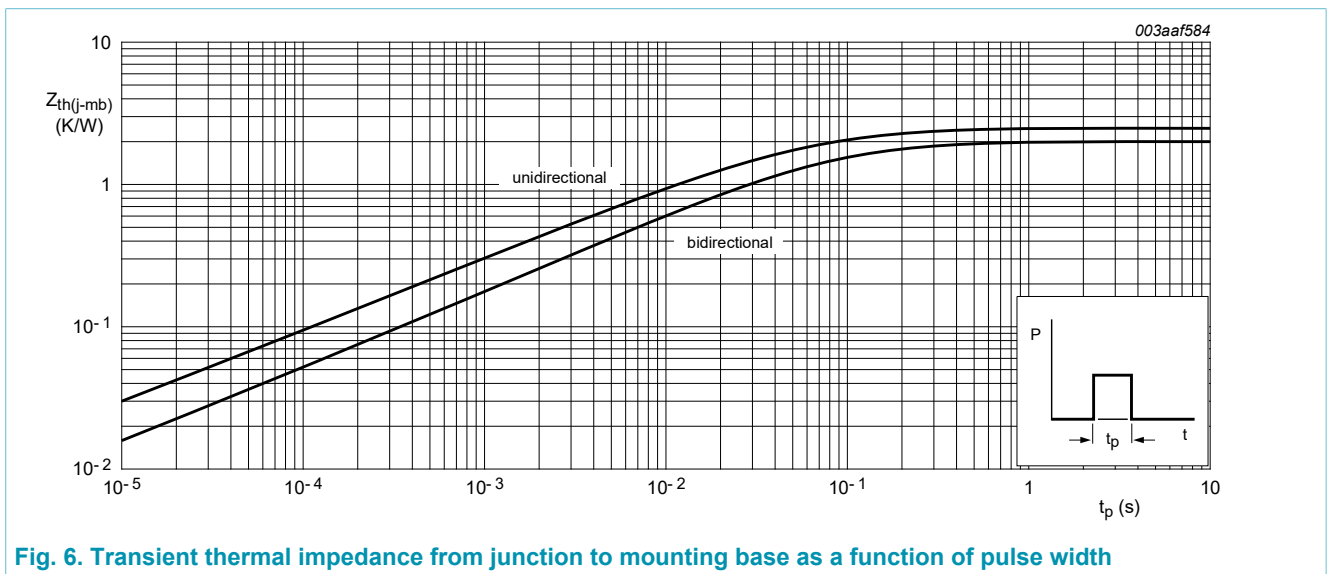
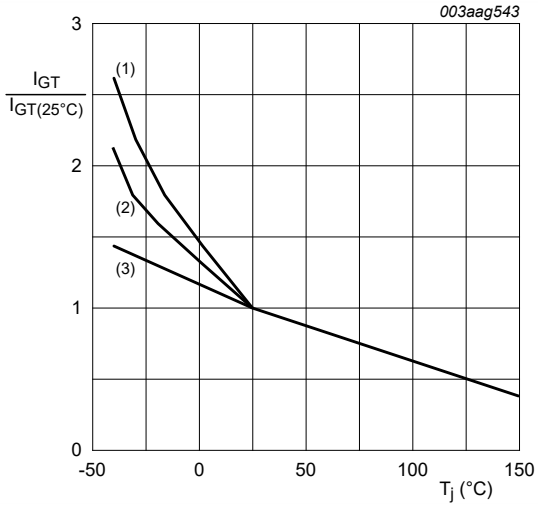


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

## 9. Characteristics

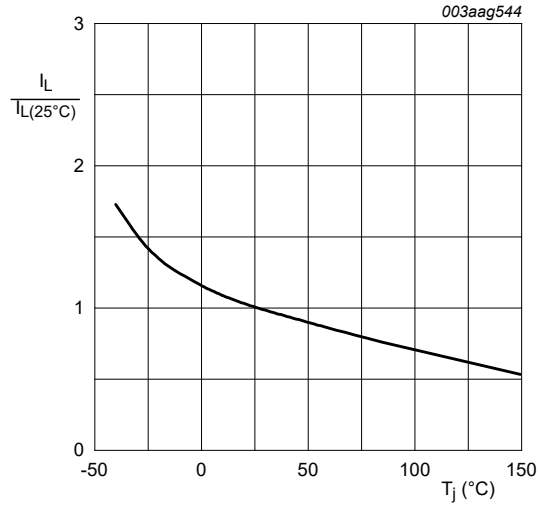
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	4	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	4	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	4	-	35	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	60	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	50	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	35	mA
$V_T$	on-state voltage	$I_T = 7\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	1.3	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	0.8	1	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 150\text{ °C}$	0.25	-	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_j = 150\text{ °C}$	-	0.4	2	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 150\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 150\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit	10	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 150\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit	12	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 150\text{ °C}$ ; $I_{T(RMS)} = 6\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit	20	-	-	A/ms

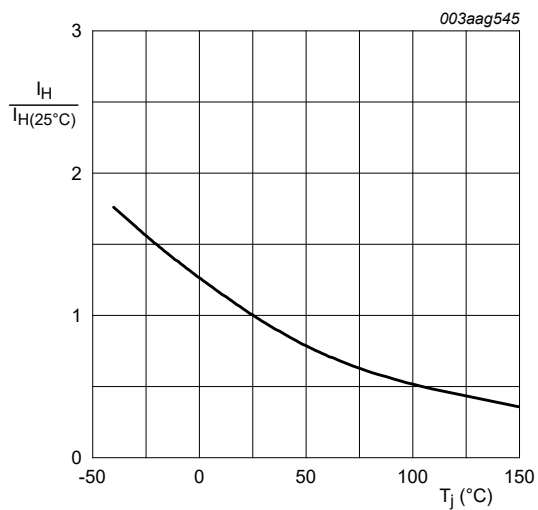


- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

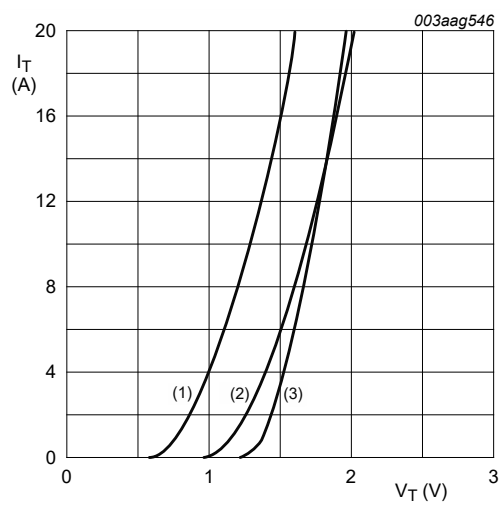
**Fig. 7. Normalized gate trigger current as a function of junction temperature**



**Fig. 8. Normalized latching current as a function of junction temperature**



**Fig. 9. Normalized holding current as a function of junction temperature**

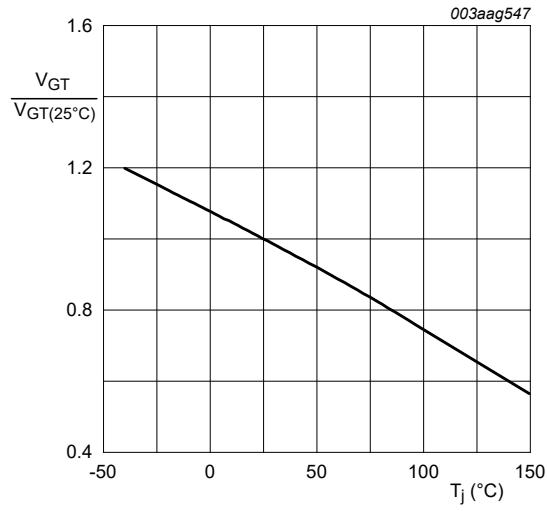


$V_o = 1.184\text{ V}; R_s = 0.047\ \Omega$

- (1)  $T_j = 150^\circ\text{C}$ ; typical values
- (2)  $T_j = 150^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25^\circ\text{C}$ ; maximum values

**Fig. 10. On-state current as a function of on-state voltage**



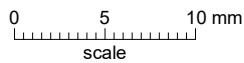
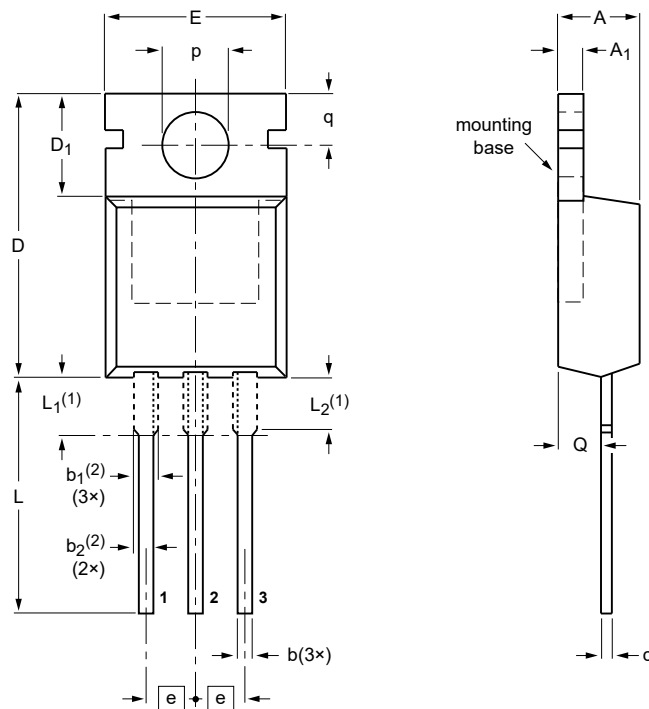


**Fig. 11. Normalized gate trigger voltage as a function of junction temperature**

## 10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



**DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> ( <sup>2</sup> )	b <sub>2</sub> ( <sup>2</sup> )	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> ( <sup>1</sup> )	L <sub>2</sub> ( <sup>1</sup> ) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

**Notes**

- Lead shoulder designs may vary.
- Dimension includes excess dambar.

**IMPORTANT NOTICE – PLEASE READ CAREFULLY**

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